



CHENMKO ENTERPRISE CO.,LTD

Halogens free devices

SURFACE MOUNT

N-Channel Enhancement Mode Field Effect Transistor

VOLTAGE 60 Volts CURRENT 500 mAmpere

CHM1702XGP

FEATURE

- * Small surface mounting type. (SC-62/SOT-89)
- * High density cell design for extremely low $R_{DS(ON)}$.
- * Rugged and reliable.
- * High saturation current capability.

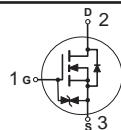
CONSTRUCTION

- * N-Channel Enhancement

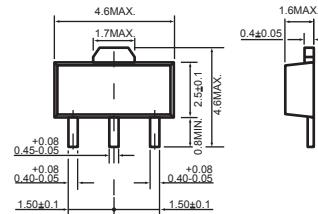
MARKING

- * 1702

CIRCUIT



SC-62/SOT-89



Dimensions in millimeters

SC-62/SOT-89

Absolute Maximum Ratings

$T_A = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	CHM1702XGP	Units
V_{DSS}	Drain-Source Voltage	60	V
V_{GSS}	Gate-Source Voltage	± 20	V
I_D	Maximum Drain Current - Continuous	500	mA
	- Pulsed (Note 3)	800	
P_D	Maximum Power Dissipation	2	W
T_J	Operating Temperature Range	-55 to 150	$^\circ\text{C}$
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ\text{C}$

Note : 1. Surface Mounted on FR4 Board , $t \leq 10\text{sec}$

2. Pulse Test , Pulse width $\leq 300\text{us}$, Duty Cycle $\leq 2\%$

3. Repetitive Rating , Pulse width limited by maximum junction temperature

4. Guaranteed by design , not subject to production testing

RATING CHARACTERISTIC CURVES (CHM1702XGP)

Electrical Characteristics $T_A = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Conditions	Min	Typ	Max	Units
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OFF CHARACTERISTICS

BV_{DSS}	Drain-Source Breakdown Voltage	$V_{\text{GS}} = 0 \text{ V}, I_D = 10 \mu\text{A}$	60			V
$I_{\text{DS}(\text{SS})}$	Zero Gate Voltage Drain Current	$V_{\text{DS}} = 60 \text{ V}, V_{\text{GS}} = 0 \text{ V}$			0.5	μA
I_{GSSF}	Gate-Body Leakage	$V_{\text{GS}} = 20\text{V}, V_{\text{DS}} = 0 \text{ V}$			+0.5	μA
I_{GSSR}	Gate-Body Leakage	$V_{\text{GS}} = -20\text{V}, V_{\text{DS}} = 0 \text{ V}$			-0.5	μA

ON CHARACTERISTICS (Note 2)

$V_{\text{GS}(\text{th})}$	Gate Threshold Voltage	$V_{\text{DS}} = 10\text{V}, I_D = 1\text{mA}$	1.5	2.0	2.5	V
$R_{\text{DS}(\text{ON})}$	Static Drain-Source On-Resistance	$V_{\text{GS}}=10\text{V}, I_D=0.3\text{A}$		1.8	2.2	Ω
g_{FS}	Forward Transconductance	$V_{\text{DS}} = 10\text{V}, I_D = 0.5\text{A}$	280	320		mS